

U.S. DEPARTMENT OF COMMERCE
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(Use several sheets if necessary)

APPLICANT MAMORU UCHIDA

FILING DATE December 26, 2001

GROUP 2878 2878

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
PL	5,835,646	11/10/98	Yoshimura et al.	385	14	
PL	6,097,472	8/1/00	Tanaka et al.	355	47	
.PL	2001-0032984	10/25/01	Uchida	274	84	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
PL	59-75656	4/28/84	Japan			Partial Translation and Abstract
PL	8-220357	8/30/96	Japan			Abstract
PL	9-96746	4/8/97	Japan			Abstract
PL	9-270751	10/14/97	Japan			Yes
PL	10-294254	11/4/98	Japan			Abstract
PL	11-54406	2/26/99	Japan			Abstract
PL	11-72750	3/16/99	Japan			Yes
PL	11-111609	4/23/99	Japan			Abstract
PL	11-196069	7/21/99	Japan			Abstract
PL	2000-31189	1/28/00	Japan			Abstract
PL	2000-31190	1/28/00	Japan			Abstract
PL	2000-235127	8/29/00	Japan			Abstract
PL	2000-337872	12/8/00	Japan			Abstract
PL	2001-284635	10/12/01	Japan			Abstract

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

PL	"GaN FETs For Microwave and High-temperature Applications", Steven C. Binari, K. Doverspike, G. Elner, H.B. Dietrich and A.E. Wickenden. Naval Research Laboratory, Washington, DC 20375-5320, USA
PL	"High-temperature Reliability of GaN Metal Semiconductor Field-Effect Transistor and Bipolar Junction Transistor" Seikoh Yoshida and Joe Suzuki, Yokohama R&D Laboratories, The Furukawa Electric Co., Ltd. 2-4-3, Okano, Nishi-ku, Yokohama, 220 Japan

EXAMINER

DATE CONSIDERED

3/28/2003